

INFORMATION DISCLOSURE CITATION PTO-1449 <small>AUG 23 2004</small>	Attorney Docket Number. 011267	Serial No. 09/960,296
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	Filing Date: September 24, 2001	Group Art Unit: 2813

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Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
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<i>JK</i>	Lee Chang et al.: "Single and Multilayer Ferroelectric PbZrxTi1-x03 (PZT) on BaTi03", Thin Solid Films, Elsevier-Sequoia S.A. Lausanne, CH., vol. 303, no. 1-2, July 15, 1997, pgs. 94-100, XP004087618 ISSN: 0040-6090, page 98, paragraph 2; figure 5.
<i>JK</i>	Inoue et al.: "Low Thermal-Budget Fabrication of Sputtered-PZT Capacitor on Multilevel Interconnects for Embedded FeRAM, Silicon Systems REs. Labs. And ULSI Development Div., NEC 2000 IEEE
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11/9/04